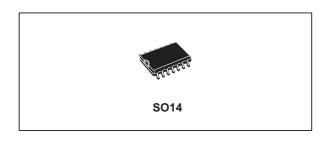


Quad exclusive OR gate

Datasheet - production data



Features

- Medium-speed operation
 t_{PHL} = t_{PLH} = 70 ns (typ) at C_L = 50 pF and
 V_{DD} = 10 V
- · Quiescent current specified up to 20 V
- 5 V, 10 V and 15 V parametric ratings
- Input leakage current
 I_I = 100 nA (max) at V_{DD} = 18 V, T_A = 25 °C
- · 100% tested for quiescent current
- ESD performance

HBM: 2 kVMM: 200 VCDM: 1 kV

Applications

- Automotive
- Industrial
- Computer
- Consumer

Description

The HCF4070 is a monolithic integrated circuit fabricated in metal oxide semiconductor technology available in an SO14 package.

The HCF4070 contains four independent exclusive OR gates. This device provides the system designer with a means for direct implementation of the exclusive OR gate for applications such as logical comparators, adders/subtractors, parity generators and checkers.

Table 1. Device summary

Order code	Temperature range	Package	Packing	Marking
HCF4070M013TR	–55 °C to +125 °C	SO14	Tape and reel	HCF4070
HCF4070YM013TR ⁽¹⁾	–40 °C to +125 °C	SO14 (automotive grade)	Tape and reer	HCF4070Y

Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q002 or equivalent.

Contents HCF4070

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HCF4070 Device overview

1 Device overview

Figure 1. Pin connections

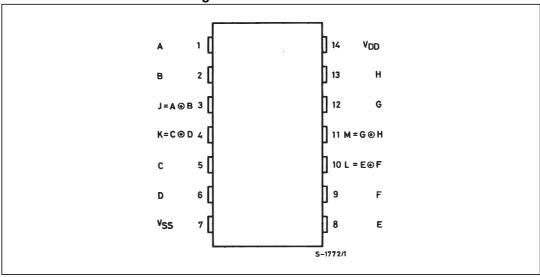
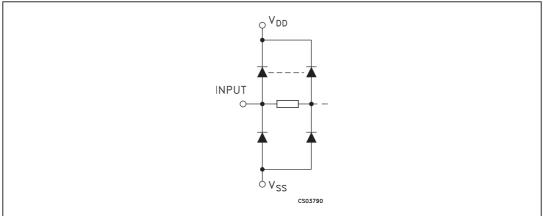


Table 2. Pin description

Pin number	Symbol/name	Function
1, 5, 8, 12	A, C, E, G	Data inputs
2, 6, 9, 13	B, D, F, H	Data inputs
3, 4, 10, 11	J, K, L, M	Data outputs
7	V _{SS}	Negative supply voltage
14	V_{DD}	Positive supply voltage

Figure 2. Input equivalent circuit



Device overview HCF4070

Figure 3. Logic diagram

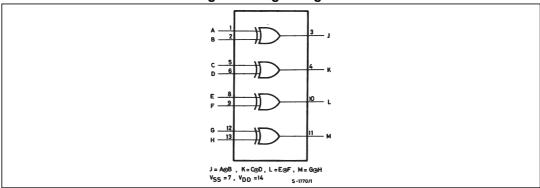


Table 3. Truth table

Inp	Output	
A, C, E, G	J, K, L, M	
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DD}	Supply voltage	-0.5 to +22	V
V _I	DC input voltage	-0.5 to V _{DD} + 0.5	V
l _l	DC input current	± 10	mA
В	Power dissipation per package	200	mW
P _D	Power dissipation per output transistor	100	mW
T _{op}	Operating temperature	-55 to +125	°C
T _{stg}	Storage temperature	-65 to +150	°C

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are relative to the V_{SS} pin voltage.

Table 5. Recommended operating conditions

Symbol	Par	ameter	Value	Unit
V_{DD}	Supply voltage		3 to 20	V
VI	Input voltage		0 to V _{DD}	V
т	Operating temperature	SO14	-55 to 125	°C
T _{op}	Operating temperature	SO14 (automotive grade)	-40 to 125	°C

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HCF4070 Device overview

Table 6. DC specifications

		Test condition			Value								
Sym.	Parameter	Parameter V _I		ΙΙ _Ο Ι	V_{DD}	T _A = 25°C		-40 to	85°C	-55 to 125°C		Unit	
		(V)	V _O (V)	(μ A)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
		0/5			5		0.02	1		30		30	
	Quiescent current	0/10			10		0.02	2		60		60	μΑ
I _L	Quiescent current	0/15			15		0.02	4		120		120	
		0/20			20		0.04	20		600		600	
		0/5		<1	5	4.95			4.95		4.95		
V _{OH}	High-level output voltage	0/10		~ 1	10	9.95			9.95		9.95] v
	J	0/15		<1	15	14.95			14.95		14.95		
		5/0		<1	5		0.05			0.05		0.05	
V _{OL}	Low-level output voltage	10/0		<1	10		0.05			0.05		0.05	v
	J	15/0		<1	15		0.05			0.05		0.05	
			0.5/4.5	<1	5	3.5			3.5		3.5		V
V _{IH}	High-level input voltage		1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
			4.5/0.5	< 1	5			1.5		1.5		1.5	
V _{IL}	Low-level input voltage		9/1	<1	10			3		3		3	v
	, and the second		13.5/1.5	<1	15			4		4		4	
		0/5	2.5	< 1	5	-1.36	-3.2		-1.15		-1.1		
lau	Output drive current	0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		mA
I _{OH}	Output drive current	0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
		0/5	0.4	<1	5	0.44	1		0.36		0.36		
I _{OL}	Output sink current	0/10	0.5	<1	10	1.1	2.6		0.9		0.9		mA
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		<u> </u>
I _I	Input leakage current	0/18	Any In	out	18		±10 ⁻⁵	±0.1		±1		±1	μА
C _I	Input capacitance		Any In	out			5	7.5					pF

The noise margin for both the "1" and "0" level is: 1 V min. with V_{DD} = 5 V, 2 V min. with V_{DD} = 10 V, 2.5 V min. with V_{DD} = 15 V.

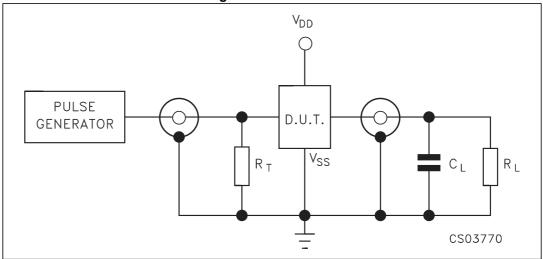
Device overview HCF4070

Table 7. Dynamic electrical characteristics (T_{amb} = 25 °C, C_L = 50 pF, R_L = 200 k Ω , t_r = t_f = 20 ns)

Symbol	Parameter	Test condition		Unit		
	raiameter	V _{DD} (V)	Min.	Тур.	Max.	Oilit
		5		140	280	
t _{PLH} t _{PHL}	Propagation delay time	10		70	130	ns
		15		50	100	
		5		100	200	
t _{TLH} t _{THL}	Output transition time	10		50	100	ns
		15		40	80	

^{1.} Typical temperature coefficient for all V_{DD} values is 0.3%/°C.

Figure 4. Test circuit



- 1. $C_L = 50$ pF or equivalent (includes jig and probe capacitance)
- 2. R_L = 200 kΩ
- 3. $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

HCF4070 Device overview

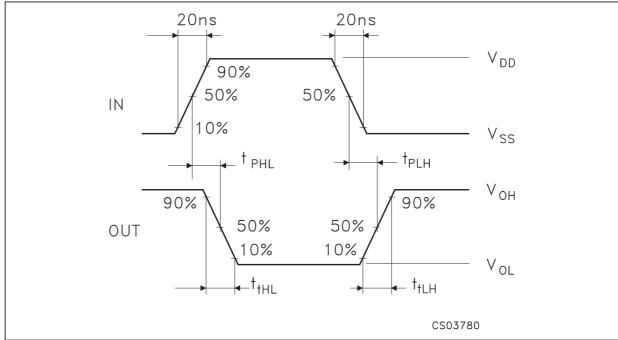


Figure 5. Waveform - propagation delay times (f = 1 MHz; 50% duty cycle)



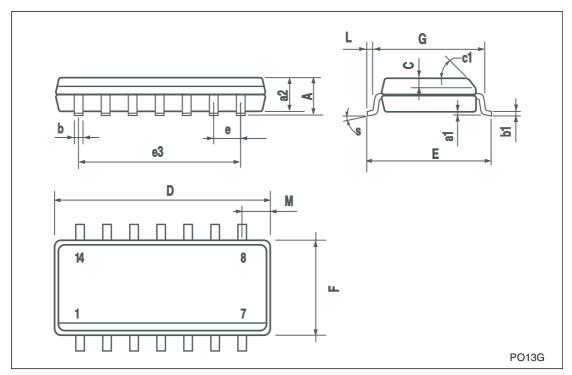
2 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.



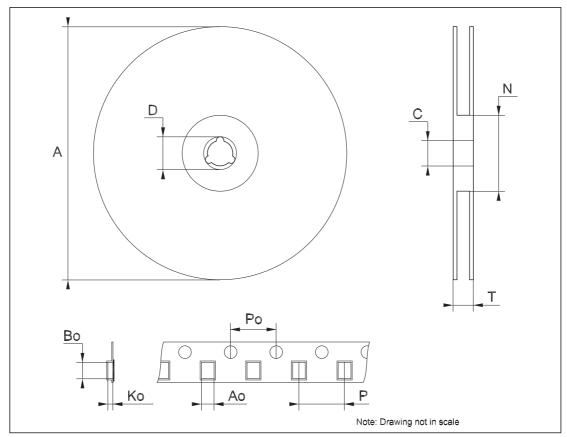
SO-14 MECHAN	NICA	۱L۸	DATA
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DIM	mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1			45°	(typ.)	•		
D	8.55		8.75	0.336		0.344	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		7.62			0.300		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.68			0.026	
S			8° (r	nax.)		•	





DIM		mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			330			12.992		
С	12.8		13.2	0.504		0.519		
D	20.2			0.795				
N	60			2.362				
Т			22.4			0.882		
Ao	6.4		6.6	0.252		0.260		
Во	9		9.2	0.354		0.362		
Ko	2.1		2.3	0.082		0.090		
Po	3.9		4.1	0.153		0.161		
Р	7.9		8.1	0.311		0.319		



HCF4070 Revision history

3 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-Jun-2012	3	Added Applications on page 1 Updated Table 1: Device summary Revised document presentation, minor textual updates
15-Jun-2012	4	Updated temperature range in <i>Table 1</i> Updated T _{op} in <i>Table 4</i> and <i>5</i>
06-Jan-2014	5	Removed DIP package option Added ESD performance to Features Added packing and marking to Table 1: Device summary Updated footnote 1 of Table 1: Device summary

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